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PATENT ✓

Customer No. 22,852  
Attorney Docket No. 08038.0032

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
)  
Takayuki NIUYA et al. ) Group Art Unit: 2823  
)  
Application No.: 09/658,193 ) Examiner: J. J. MALDONADO  
)  
Filed: September 8, 2000 )  
)  
For: METHOD AND APPARATUS FOR )  
PRODUCING SEMICONDUCTOR )  
DEVICE )

Assistant Commissioner for Patents  
Washington, DC 20231

Sir:

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TECHNOLOGY CENTER 2800

AMENDMENT

In reply to the Office Action dated May 13, 2002, the period for reply having been extended for three months by a request for extension and fee payment filed concurrently herewith, please amend the application as follows:

IN THE CLAIMS:

Please amend claims 11, 14, 16, and 21, as follows:

11. (Amended) A method of manufacturing a semiconductor device, comprising the steps of:
- making a first concavity in a first insulating film of the device;
  - covering the first concavity with a first barrier layer for preventing metal diffusion;
  - burying the first concavity covered with the first barrier layer with a wiring metal;

B'  
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